

Comment on "Experimental determination of superconducting parameters for the intermetallic perovskite superconductor MgCNi_3 "

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In a recent paper (Phys. Rev. **B 67**, 094502 (2003)) Mao *et al.* investigated the bias-dependent conductance of mechanical junctions between superconducting MgCNi_3 and a sharp W tip. They interpreted their results in terms of 'single-particle tunneling'. We show it is more likely that current transport through those junctions is determined by thermal effects due to the huge normal-state resistivity of MgCNi_3 . Therefore no conclusion can be drawn about the possible unconventional pairing or strong-coupling superconductivity in MgCNi_3 .

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In a recent paper Mao *et al.*¹ reported bulk transport and specific heat measurements on superconducting MgCNi_3 . Additionally, they investigated the conductance of mechanical junctions between superconducting MgCNi_3 and a sharp W tip with $15\text{ }\mu\text{m}$ curvature radius. By postulating that tunneling dominates the conductance they interpreted the observed zero-bias conductance peak (ZBCP) as caused by Andreev-bound states which result from a possible unconventional pairing state in MgCNi_3 . Besides that, Mao *et al.*¹ attributed the simultaneously appearing two conductance dips to the characteristic superconducting energy scale in MgCNi_3 . On this basis Mao *et al.* suggested that 'this result can be taken as further support of strong-coupling superconductor of MgCNi_3 '.

We believe that before dealing with more exotic phenomena, like Andreev-bound states, more trivial effects should be considered to explain the observed conductance anomalies of those junctions.

Firstly, Mao *et al.*¹ assumed that a tunneling barrier forms at their junctions with rather low resistance $< 0.1\Omega$. This assumption was based only on the fact that the shape of the superconducting transition in the resistance $R(T)$ of the junctions deviates from that of the bulk resistivity $\rho(T)$. According to our experience, such deviations are typical for mechanical junctions (or point contacts) with highly resistive metals. The sharp tip damages the sample surface in the contact area, that means the material there is more degraded than in the bulk. This can locally change ρ as well as T_c . Fig. 1 shows as example the behavior of $R(T)$ for several contacts between an amorphous superconducting Zr_2Ni ribbon (its residual normal-state resistivity $\rho_0 \approx 170\text{ }\mu\Omega\text{cm}$ is comparable to that of MgCNi_3) and a Cu tip². While $R(T)$ of low-ohmic contacts has a rather sharp transition similar to that of $\rho(T)$, the transition broadens for larger R_N . The same kind of broadening was observed for URu_2Si_2 break junctions³ (also a metal with large ρ). In the latter ex-

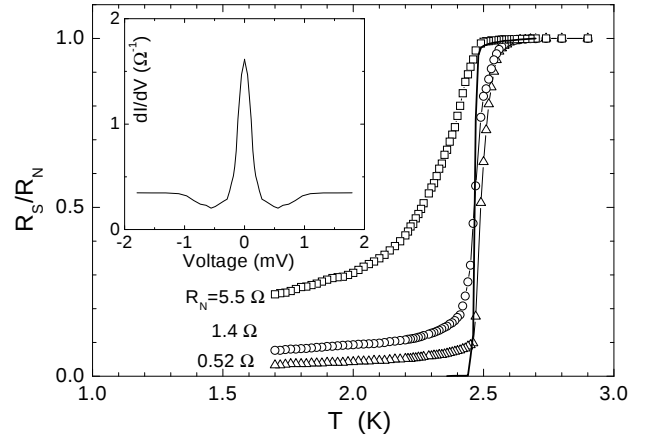


FIG. 1: Temperature dependence of the differential resistance at zero bias ($R \equiv dV/dI(V=0)$) of three junctions between an amorphous Zr_2Ni ribbon and a Cu tip (open symbols, redrawn from Ref. 2). The solid line shows the bulk resistance of the Zr_2Ni ribbon. All curves are normalized to the normal-state resistance R_N , which is also indicated for each junction. Inset: Numerically derived from IVC in Ref. 2 differential conductance $dI/dV(V)$ at 1.7 K of one of the ZrNi_2 -Cu contacts.

periments breaking the samples at helium temperatures prevented the formation of any oxide or other contaminating layer on the surface which could otherwise produce a tunneling barrier.

Secondly, ZBCPs are characteristic features of junctions formed with superconductors that have a high normal-state resistivity, as shown in the inset of Fig. 1 for a ZrNi_2 - Cu contact. As another example, Gloos *et al.*⁴ observed pronounced zero-bias minima in dV/dI (corresponding to ZBCPs in dI/dV) for contacts between the heavy-fermion superconductor UBe_{13} and a W tip (UBe_{13} also has a very high resistivity, comparable to that of MgCNi_3). They concluded that the dV/dI anomalies were due to diffusive and thermal transport through the junctions, while significant Andreev reflection currents were missing.

Thirdly, MgCNi_3 has a huge residual resistivity $\rho_0 \approx$

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400 $\mu\Omega\text{cm}$ (see the inset of Fig. 3 in Ref. 1) like that of amorphous metals. With the carrier density $n \approx 10^{28}\text{ m}^{-3}$ from Ref. 6 and the Drude formula $l = \hbar k_F / (e^2 n \rho)$, where k_F is the Fermi wave number, we calculate an elastic electron mean free path (mfp) $l_{el} \approx 0.7\text{ nm}$. This is comparable to the lattice constant. The inelastic mfp $l_{in} \sim \hbar v_F / k_B T \approx 1.5\text{ }\mu\text{m}$ at 1 K according to Ref. 5. Here v_F is the Fermi velocity. This results in a very small diffusive inelastic mfp $\Lambda \approx \sqrt{l_{el} l_{in}} \approx 30\text{ nm}$. Applying the Maxwell formula that describes the spreading resistance of large metallic contacts

$$R_N \approx \rho / 2d \quad (1)$$

and taking into account that W has a negligibly small resistivity compared to that in MgCNi_3 we estimate a contact radius $r = d/2$ between 12-20 μm for the junctions presented in Ref. 1. *This fits very well the curvature of the W tip (15 μm), supporting our model of a direct metallic contact!* Since d is much larger than the diffusive inelastic electronic mfp Λ , these contacts are in the thermal regime⁷ in which the temperature inside the contact rises with applied bias voltage, and the differential conductance depends only on $\rho(T)$ ⁷. In the thermal regime the bias voltage does no longer determine the excess energy of the electrons. And this makes it impossible to obtain any spectral information about the transport processes through the junctions and seriously questions the conclusions in Ref. 1 with respect to the characteristic superconducting energy scale in MgCNi_3 .

Fourthly, the current density can be quite large for the contacts investigated in Ref. 1. For example at $V = 1\text{ mV}$ the current density is larger than $j = V / (R_N d^2) \simeq 10^7\text{ A/m}^2$. The ZBCPs, the abrupt decrease of dI/dV with increasing bias voltage, are very likely caused by the continuous growth of the normal phase due to the temperature rise inside the constriction discussed above as well as due to the increasing current density.⁹ The pulsed-current method used by Mao *et al.*¹ to measure the $I - V$ curves with a pulse duration of $t = 5 \cdot 10^{-2}\text{ s}$ certainly reduces heating of the bulk sample itself, but it does not prevent local heating of the junctions. Junctions with diameters of several 10 nm typically have a thermal relaxation time $\tau \approx 10^{-9}\text{ s}$.^{7,8} Since $\tau \propto d^2$, the MgCNi_3 - W contacts with $d \approx 20 - 40\text{ }\mu\text{m}$, as estimated above, should have $\tau \sim 10^{-3}\text{ s}$. This is still much smaller than the pulse duration t , meaning that the local temperature will respond to the applied bias voltage almost without delay.

In conclusion, to obtain reliable information from point-contact experiments, the regime of current flow through the constrictions has to be properly established and/or analyzed. For junctions with highly resistive metals like MgCNi_3 thermal effects have to be expected. Apparently, they play here the role of preventing us from energy-resolved spectroscopy.

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